

Semiconductor Device Measurements (RP 4.2.16)

Fabrication of MOS capacitors and junction diodes, characterization of MOS capacitors by C-V and I-V, determination of electrical parameters of MOSFETs like threshold voltage, subthreshold slope and drain induced barrier lowering (DIBL), determination of device parameters related to circuit applications, measurement of Hall mobility, fabrication of Schottky contact and measurement of barrier height, PL measurements.